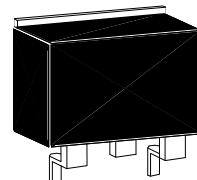


## N -Channel Logic Level Enhancement Mode Power MOSFET

### Features:

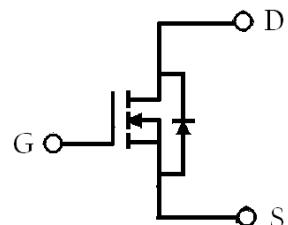
- Low Gate Charge
- Simple Drive Requirement
- Pb-free lead plating package

TO-263



G D S

<b>BVDSS</b>	<b>150V</b>
<b>ID @ VGS=10V, Tc=25°C</b>	<b>20A</b>
<b>RDS(ON)@ VGS=10V, ID=15A</b>	<b>66mΩ(typ)</b>
<b>RDS(ON)@ VGS=5V, ID=10A</b>	<b>64mΩ(typ)</b>
<b>RDS(ON)@ VGS=3V, ID=3A</b>	<b>66mΩ(typ)</b>



G : Gate D : Drain S : Source

### Ordering Information

Device	Package	Shipping
KWN6515F3	TO-263 (Pb-free lead plating and RoHS compliant package)	800 pcs / Tape & Reel

### Absolute Maximum Ratings ( $T_c=25^\circ C$ , unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	$V_{DS}$	150	<b>V</b>
Gate-Source Voltage	$V_{GS}$	$\pm 16$	
Continuous Drain Current @ $T_c=25^\circ C$ , $V_{GS}=10V$	$I_D$	20	<b>A</b>
Continuous Drain Current @ $T_c=100^\circ C$ , $V_{GS}=10V$		14	
Pulsed Drain Current *1	$I_{DM}$	60	<b>A</b>
Avalanche Current	$I_{AS}$	20	
Avalanche Energy @ $L=0.14mH$ , $I_D=20A$ , $R_G=25\Omega$	$E_{AS}$	28	<b>mJ</b>
Repetitive Avalanche Energy @ $L=0.05mH$ *2	$E_{AR}$	10	
Total Power Dissipation @ $T_c=25^\circ C$	$P_d$	100	<b>W</b>
Total Power Dissipation @ $T_c=100^\circ C$		50	
Operating Junction and Storage Temperature Range	$T_j$ , $T_{stg}$	-55~+175	<b>°C</b>

Note : \*1. Pulse width limited by maximum junction temperature

\*2. Duty cycle  $\leq 1\%$

### Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	1.5	<b>°C/W</b>
Thermal Resistance, Junction-to-ambient, max*	$R_{th,j-a}$	40	
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	62.5	

\*When mounted on the minimum pad size (PCB mount),  $t \leq 10s$ .

### Characteristics ( $T_c=25^\circ C$ , unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
<b>Static</b>					
$V_{GS(th)}$	0.45	0.8	1.20	<b>V</b>	$V_{DS}=V_{GS}$ , $I_D=250\mu A$
$I_{GSS}$	-	-	$\pm 100$	$nA$	$V_{GS}=\pm 16V$ , $V_{DS}=0V$
$I_{DSS}$	-	-	1	$\mu A$	$V_{DS}=120V$ , $V_{GS}=0V$
	-	-	25		$V_{DS}=100V$ , $V_{GS}=0V$ , $T_J=125^\circ C$
$R_{DS(ON)} *1$	-	66	75	$m\Omega$	$V_{GS}=10V$ , $I_D=15A$
	-	64	75		$V_{GS}=5V$ , $I_D=10A$
	-	66	75		$V_{GS}=3V$ , $I_D=3A$
$G_{FS} *1$	-	43	-	<b>S</b>	$V_{DS}=5V$ , $I_D=10A$
<b>Dynamic</b>					
$Q_g *1, 2$	-	30	-	<b>nC</b>	$I_D=10A$ , $V_{DS}=80V$ , $V_{GS}=5V$
$Q_{gs} *1, 2$	-	4.8	-		
$Q_{gd} *1, 2$	-	16	-		
$t_{d(ON)} *1, 2$	-	23	-	<b>ns</b>	$V_{DS}=75V$ , $I_D=1A$ , $V_{GS}=4.5V$ , $R_G=6\Omega$
$t_r *1, 2$	-	22	-		
$t_{d(OFF)} *1, 2$	-	91	-		
$t_f *1, 2$	-	63	-		



C <sub>iss</sub>	-	2282	-	pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz
C <sub>oss</sub>	-	120	-		
C <sub>rss</sub>	-	66	-		
<b>Source-Drain Diode</b>					
I <sub>s</sub> *1	-	-	20	A	
I <sub>SM</sub> *3	-	-	60		
V <sub>SD</sub> *1	-	0.86	1.3	V	I <sub>F</sub> =I <sub>s</sub> , V <sub>GS</sub> =0V
t <sub>rr</sub>	-	50	-	ns	I <sub>F</sub> =20A, dI <sub>F</sub> /dt=100A/μs
Q <sub>rr</sub>	-	120	-	nC	

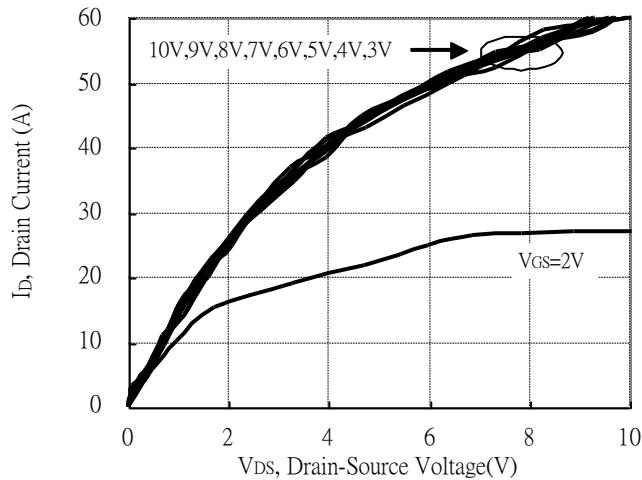
Note : \*1.Pulse Test : Pulse Width  $\leq$ 300μs, Duty Cycle $\leq$ 2%

\*2.Independent of operating temperature

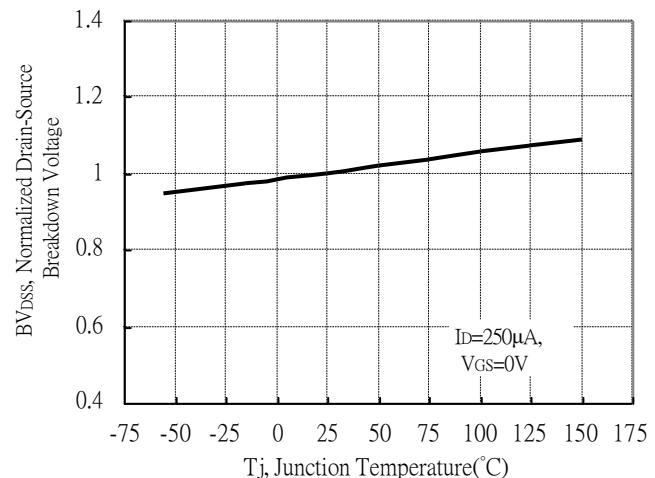
\*3.Pulse width limited by maximum junction temperature.

## Typical Characteristics

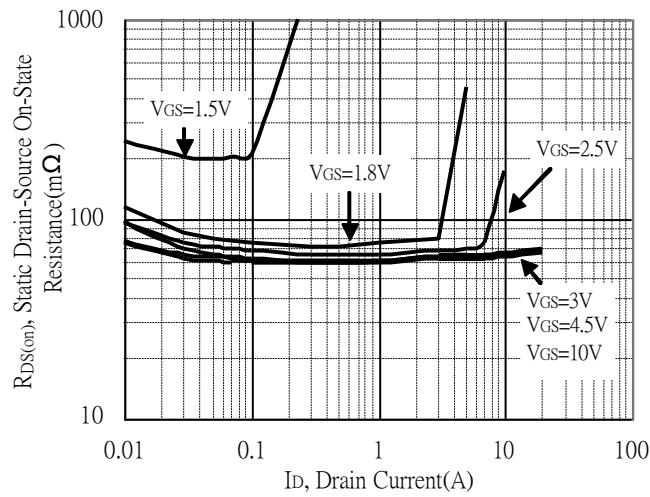
Typical Output Characteristics



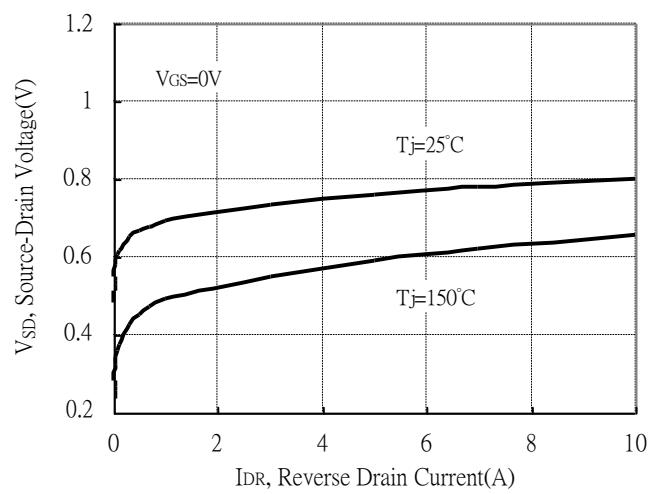
Breakdown Voltage vs Ambient Temperature



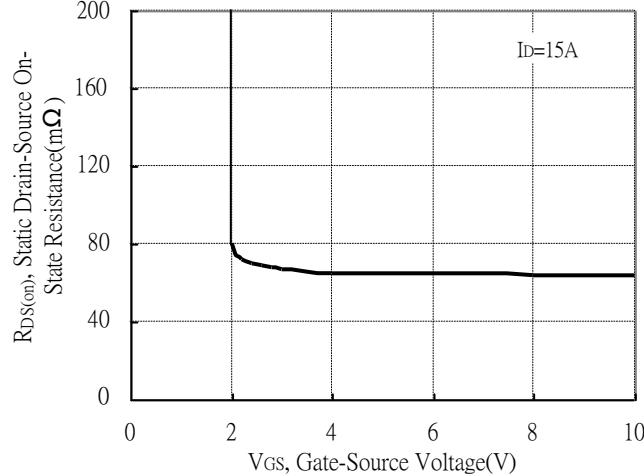
Static Drain-Source On-State resistance vs Drain Current



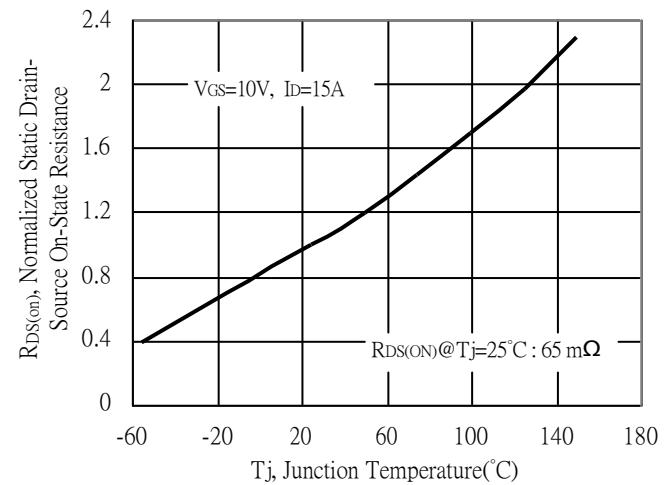
Reverse Drain Current vs Source-Drain Voltage



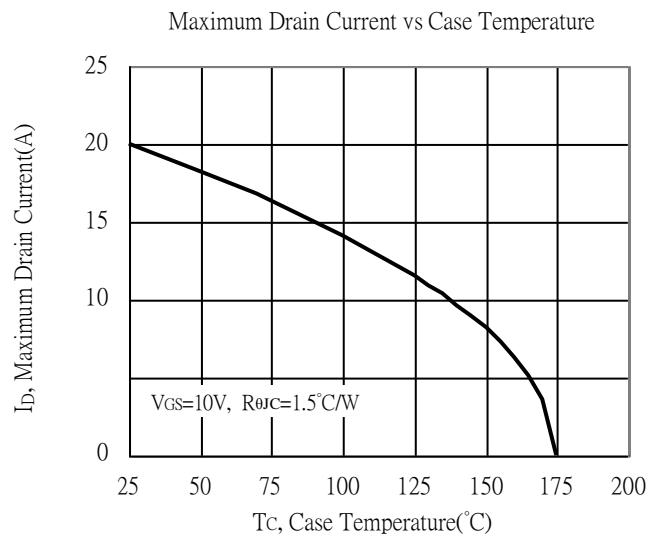
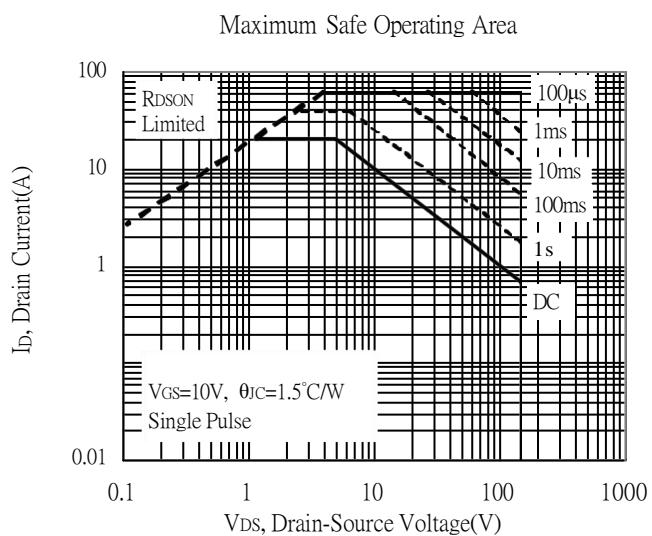
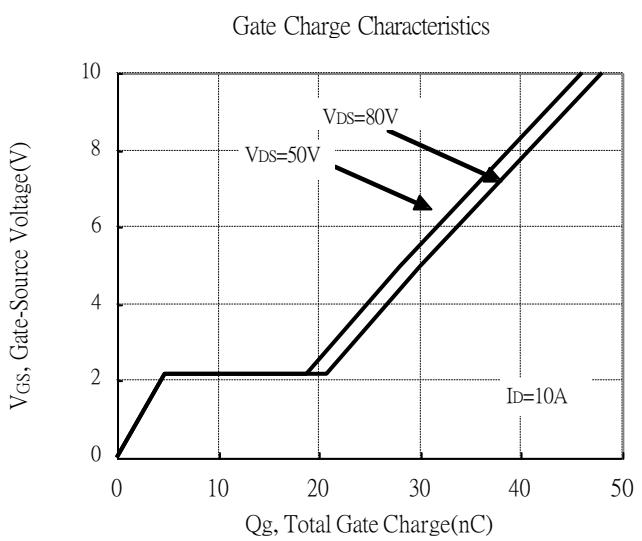
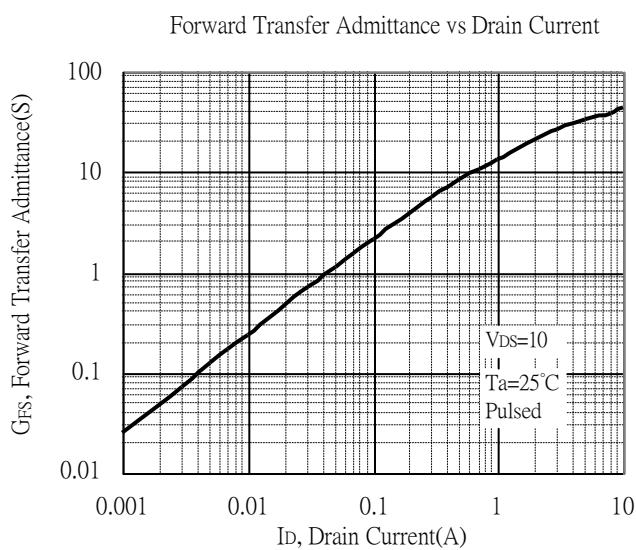
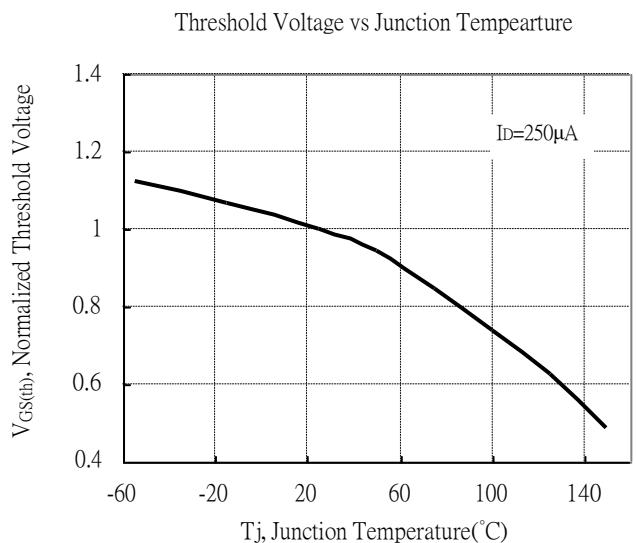
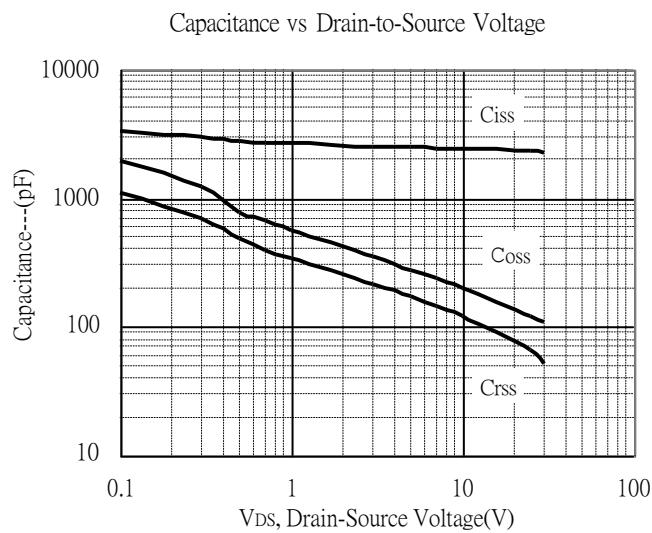
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Drain-Source On-State Resistance vs Junction Temperature

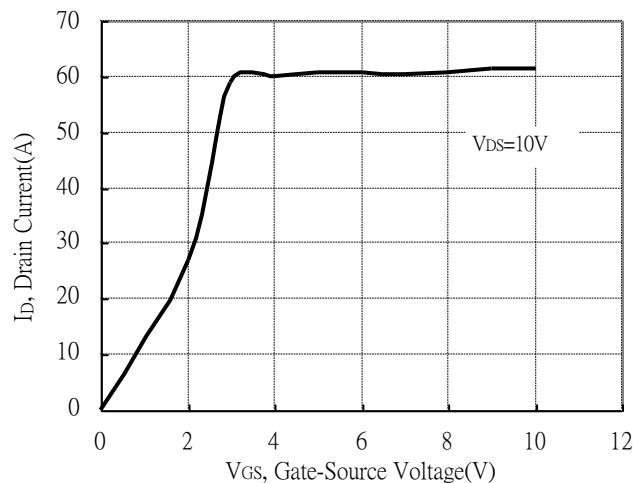


## Typical Characteristics (Cont.)

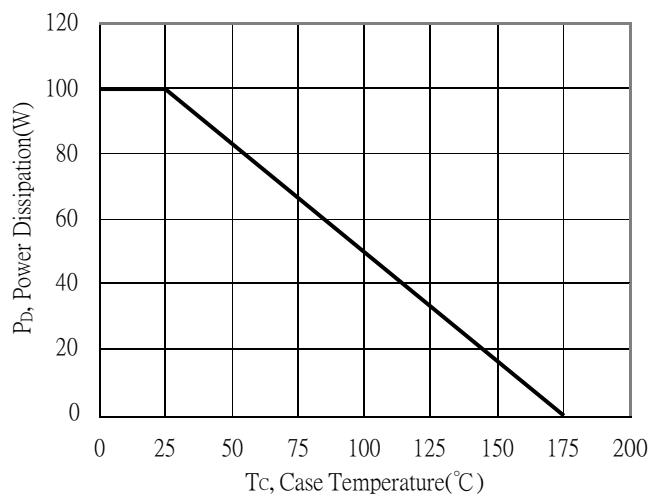


## Typical Characteristics (Cont.)

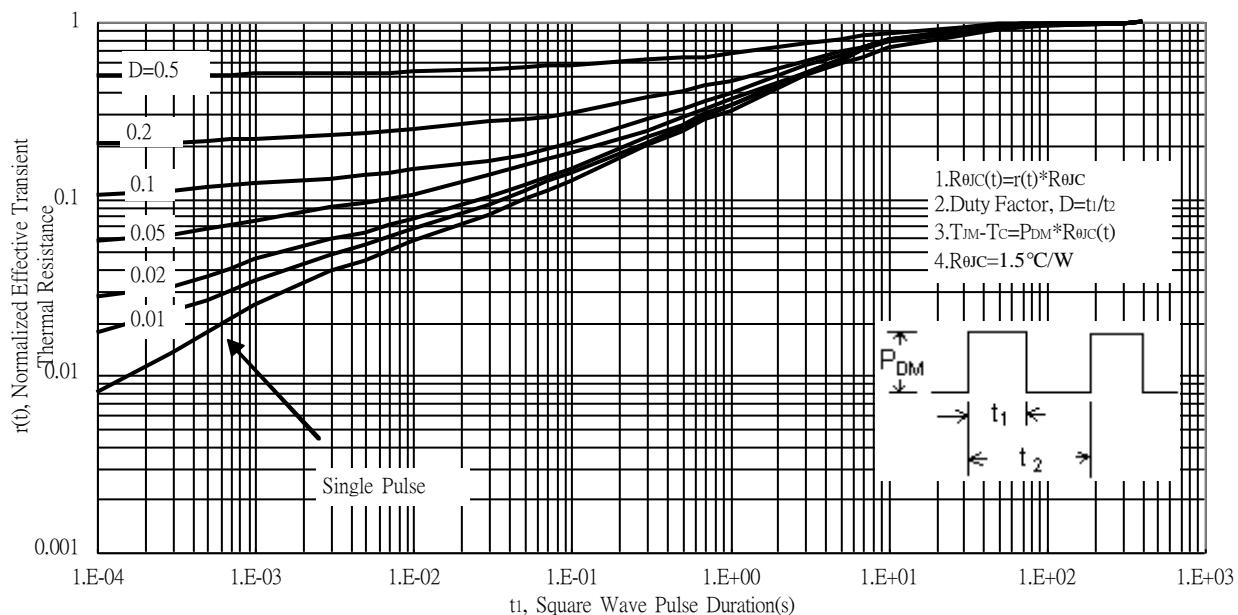
Typical Transfer Characteristics



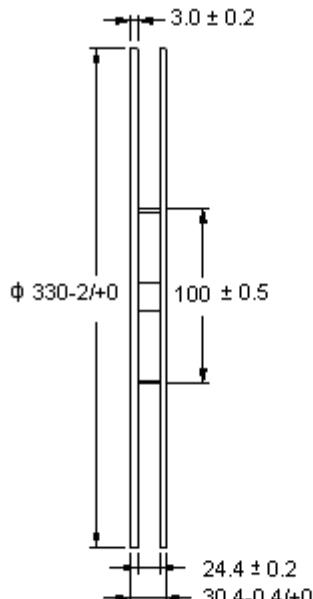
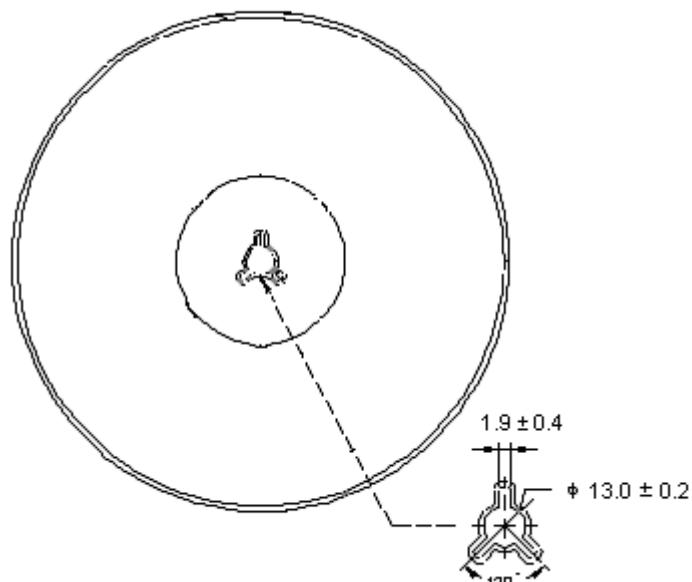
Power Derating Curve



Transient Thermal Response Curves

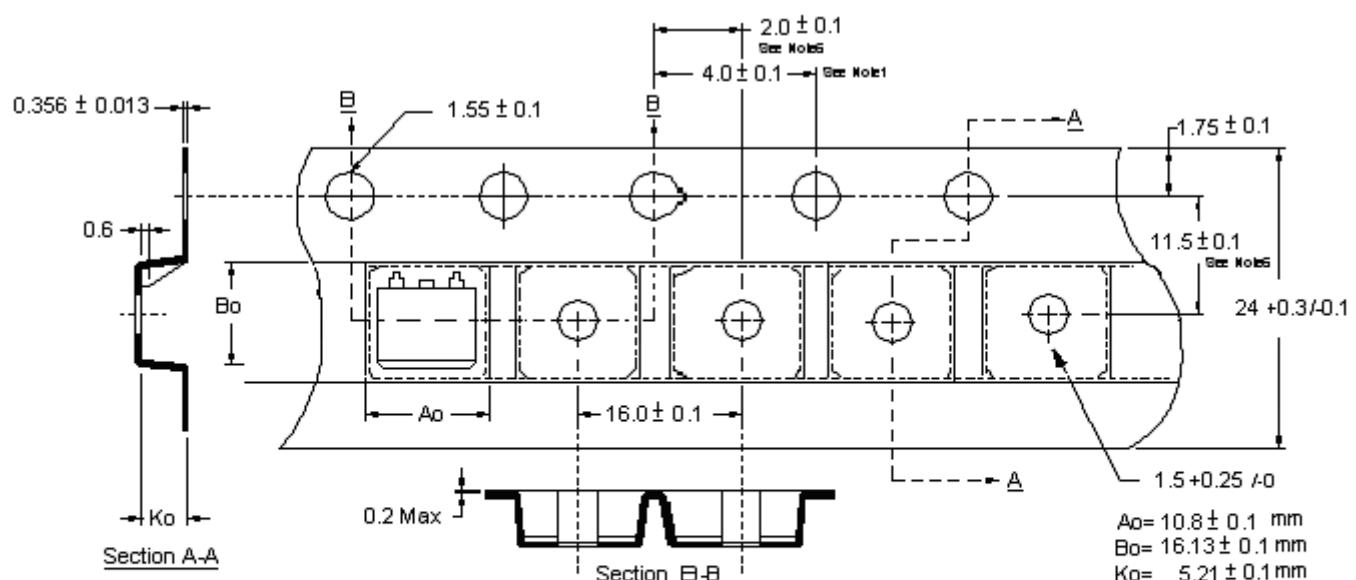


## Reel Dimension



Unit: millimeter

## Carrier Tape Dimension

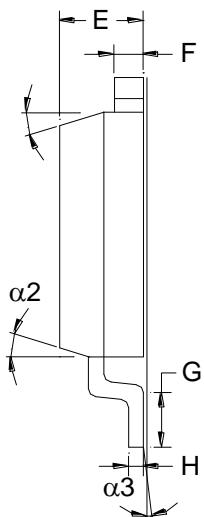
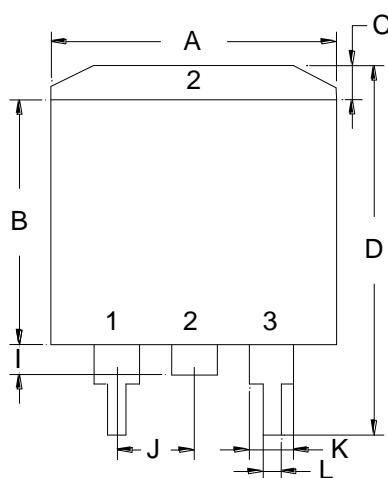


Notes:

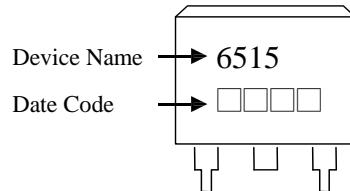
1. 10 sprocket hole pitch cumulative tolerance  $\pm 0.2$ .
2. Camber not to exceed 1mm in 100mm.
3. Material: Conductive Black Advantek Polystyrene.
4. Ao & Bo measured on a plane 0.3mm above the bottom of the pocket.
5. Ko measured from a plane on the inside bottom of the pocket to the top surface of the carrier.
6. Pocket position relative to sprocket hole measured as true position of pocket, not pocket hole.

Unit : millimeter

## TO-263 Dimension



Marking :



Style : Pin 1.Gate 2.Drain 3.Source

3-Lead Plastic Surface Mounted Package  
 Package Code : F3

\*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.3800	0.4050	9.65	10.29	I	0.0500	0.0700	1.27	1.78
B	0.3300	0.3700	8.38	9.40	J	-	*0.1000	-	*2.54
C	-	0.0550	-	1.40	K	0.0450	0.0550	1.14	1.40
D	0.5750	0.6250	14.61	15.88	L	0.0200	0.0390	0.51	0.99
E	0.1600	0.1900	4.06	4.83	alpha1	-	-	6°	8°
F	0.0450	0.0550	1.14	1.40	alpha2	-	-	6°	8°
G	0.0900	0.1100	2.29	2.79	alpha3	-	-	0°	5°
H	0.0180	0.0290	0.46	0.74					